

UNISONIC TECHNOLOGIES CO., LTD

MGBR5V45 Preliminary DIODE

MOS GATED BARRIER RECTIFIER

■ DESCRIPTION

The UTC MGBR5V45 is a surface mount mos gated barrier rectifier, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

■ FEATURES

- * Very low forward voltage drop
- * High switching speed

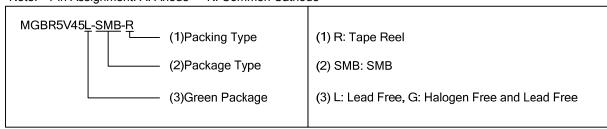
■ SYMBOL



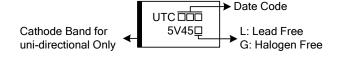
ORDERING INFORMATION

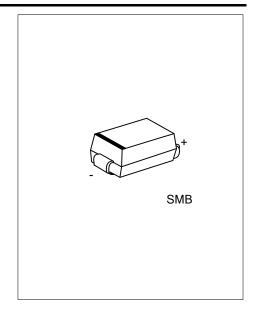
Ordering Number		Dealtons	Pin Assignment		Doolsing	
Lead Free	Halogen Free	Package	1	2	Packing	
MGBR5V45L-SMB-R	MGBR5V45G-SMB-R	SMB	K	Α	Tape Reel	

Note: Pin Assignment: A: Anode K: Common Cathode



■ MARKING





■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER	SYMBOL	RATINGS	UNIT
DC Blocking Voltage	V_{RM}	45	V
Working Peak Reverse Voltage	V_{RWM}	45	V
Repetitive Peak Reverse Voltage	V_{RRM}	45	V
RMS Reverse Voltage	$V_{R(RMS)}$	32	V
Average Rectified Output Current T _C =140°C	lo	5	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I _{FSM}	90	Α
Repetitive Peak Avalanche Power (1µs, 25°C)	P_{ARM}	5000	W
Operating Junction Temperature	T_J	-65~+150	°C
Storage Temperature	T_{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	70	°C/W

■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.5mA	45			V
Landard Francisco Francisc	V_{FM}	I _F =5A, T _J =25°C			0.61	V
Instantaneous Forward Voltage		I _F =5A, T _J =125°C			0.58	٧
Leakage Current (Note 1)	I _{RM}	V _R =45V, T _J =25°C		50	500	μA
		V _R =45V, T _J =125°C		12	15	mA
Total Capacitance	C _T	V _R =5V, f=1MHz, T _J =25°C		400		pF

Notes: 1. Short duration pulse test used to minimize self-heating effect.

^{2.} Thermal resistance junction to case mounted on heatsink.

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